CLAIMS

1. A process for trapping Silicon compounds in a gaseous or liquid feedstock, comprising bringing the feedstock into contact with a trapping mass with a liquid hourly space velocity LHSV of less than 5 h^{-1} or a gas hourly space velocity GHSV of less than 500 h^{-1}, said trapping mass comprising a metal from the group VIB metals and a metal from the group VIII metals, wherein the content of the metal from the group VIB metals, expressed as an oxide, is less than 6% by weight relative to the total weight of the trapping mass.

2. The trapping process as claimed in claim 1, wherein the liquid hourly space velocity LHSV is less than 4.5 h^{-1}, or the gas hourly space velocity GHSV is less than 450 h^{-1}.

3. The trapping process as claimed in claim 1 or claim 2, wherein the contact is carried out at a temperature of between 20°C and 500°C and a pressure of between 0.1 and 10 MPa.

4. The trapping process as claimed in any one of the preceding claims, wherein the contact is carried out in the presence of dihydrogen, wherein the feedstock is liquid and the ratio of the gaseous volume flow rate of dihydrogen to the liquid volume flow rate of liquid feedstock is between 0 and 1000 Nm^3/m^3, or wherein the feedstock is gaseous and the dihydrogen partial pressure PpH_2 is between 0.01 MPa and 10 MPa.

5. The trapping process as claimed in any one of the preceding claims, wherein the trapping mass is arranged in a fixed bed.

6. The trapping process as claimed in any one of the preceding claims, using a plurality of trapping masses positioned as a mixture or multilayer.

7. The trapping process as claimed in any one of the preceding claims, using trapping masses arranged in a trapping unit comprising at least two reactors, positioned in series or in parallel.

8. The trapping process as claimed in claim 7, wherein the operating conditions of each of the reactors are identical or different.

9. The trapping process as claimed in any one of the preceding claims, further comprising a pretreatment step upstream of the contacting step in order to reduce or eliminate unsaturated organic compounds.

10. The trapping process as claimed in claim 9, wherein the pretreatment step is a selective hydrogenation step.

11. The trapping process as claimed in any one of the preceding claims, wherein the effluent depleted in silicon compounds is sent to a hydrotreating section.

12. The trapping process as claimed in any one of the preceding claims, wherein the trapping mass is positioned at the inlet of a hydrotreating reactor.

13. The trapping process as claimed in any one of the preceding claims, wherein the trapping mass contains alumina.

14. The trapping process as claimed in any one of the preceding claims, wherein the trapping mass has at least one of the following characteristics: γ-type support, presence of group VIB metal with a content of less than 20% by weight of group VIB metal expressed as oxide, presence of group VIII metal with a content of less than 10% by weight of group VIII metal expressed as oxide, presence of phosphorus with a content of less than 15% by weight of P expressed as oxide P_2O_5, grain density at least 0.2 g/ml, specific surface area at least 200 m^2/g, average pore size of less than 50 nm, total pore volume of between 0.15 cm^3/g and 1.5 cm^3/g.

15. The trapping process as claimed in any one of the preceding claims, wherein the feedstock is chosen from the group consisting of combustion flue gases, synthesis gas, natural gas, natural-gas condensates, petroleum or petroleum crudes, liquid or gaseous petroleum cuts, liquid hydrocarbon cuts from refineries or petrochemical plants, effluents resulting from Fischer-Tropsch synthesis processes, petroleum petrochemical intermediates, oils resulting from the pyrolysis of biomass or plastics, biogas, coking gasoline or catalytic cracking gasoline, and mixtures thereof.